Guanyu Zhou

List of Publications by Year
in descending order

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20 papers	838 citations	687363 13 h-index	794594 19 g-index
20 all docs	20 docs citations	20 times ranked	1707 citing authors

#	Article	IF	Citations
1	Controlling the Pd Metal Contact Polarity to Trigonal Tellurium by Atomic Hydrogenâ€Removal of the Native Tellurium Oxide. Advanced Materials Interfaces, 2021, 8, 2002050.	3.7	10
2	WSe _(2â" x) Te _x alloys grown by molecular beam epitaxy. 2D Materials, 2019, 6, 045027.	4.4	20
3	Superconductivity above 28â€¯K in single unit cell FeSe films interfaced with GaO2â" layer on NdGaO3(1â€¯1â€¯0). Science Bulletin, 2019, 64, 490-494.	9.0	8
4	Asymmetrically optimized structure in a high-T _c single unit-cell FeSe superconductor. Journal of Physics Condensed Matter, 2019, 31, 055701.	1.8	4
5	Controlled crack propagation for atomic precision handling of wafer-scale two-dimensional materials. Science, 2018, 362, 665-670.	12.6	208
6	Interface enhanced superconductivity in monolayer FeSe films on MgO(001): charge transfer with atomic substitution. Science Bulletin, 2018, 63, 747-752.	9.0	24
7	Highâ€Mobility Helical Tellurium Fieldâ€Effect Transistors Enabled by Transferâ€Free, Lowâ€Temperature Direct Growth. Advanced Materials, 2018, 30, e1803109.	21.0	71
8	Origin of charge transfer and enhanced electronâ€"phonon coupling in single unit-cell FeSe films on SrTiO3. Nature Communications, 2017, 8, 214.	12.8	77
9	Interface induced high temperature superconductivity in single unit-cell FeSe on SrTiO3(110). Applied Physics Letters, 2016, 108, .	3.3	51
10	Atomically resolved FeSe/SrTiO ₃ (001) interface structure by scanning transmission electron microscopy. 2D Materials, 2016, 3, 024002.	4.4	50
11	Interface-enhanced electron-phonon coupling and high-temperature superconductivity in potassium-coated ultrathin FeSe films on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>SrTiO</mml:mi><mml:mn>3</mml:mn></mml:msub><m Physical Review B, 2016, 93, .	3.2	70
12	Ultrafast Dynamics Evidence of High Temperature Superconductivity in Single Unit Cell FeSe on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>SrTiO</mml:mi></mml:mrow><mml:mrow><mml:mn>3</mml:mn></ Physical Review Letters, 2016, 116, 107001.	7.8	77
13	Superconductivity dichotomy in K-coated single and double unit cell FeSe films on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>SrTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2016, 93, .	3.2	47
14	Interface-enhanced high-temperature superconductivity in single-unit-cell<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>FeT</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â"</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:mrow></ mathvariant="normal">S</mml:mi><mml:msub><mml:mi mathvariant="normal">e</mml:mi><mml:mi>x</mml:mi></mml:msub></mml:mrow></mml:math>films on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mm. Physical Review	3.2	48
15	Wetting layer evolution and its temperature dependence during self-assembly of InAs/GaAs quantum dots. Nanoscale Research Letters, 2012, 7, 600.	5.7	31
16	Effects of ultra-low Al alloying In(Al)As layer on the formation and evolution of InAs/GaAs quantum dots. Journal of Applied Physics, 2011, 109, 094311.	2.5	0
17	The transition from two-stage to three-stage evolution of wetting layer of InAs/GaAs quantum dots caused by postgrowth annealing. Applied Physics Letters, 2011, 98, 071914.	3.3	6
18	Carrier tunneling effects on the temperature dependent photoluminescence of InAs/GaAs quantum dot: Simulation and experiment. Journal of Applied Physics, 2011, 109, 083501.	2.5	17

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19	The two- to three-dimensional growth transition of InAs/GaAs epitaxy layer studied by reflectance difference spectroscopy. Journal of Applied Physics, 2010, 108, 083513.	2.5	7
20	Temperature dependent photoluminescence of an In(Ga)As/GaAs quantum dot system with different areal density. Journal Physics D: Applied Physics, 2010, 43, 295401.	2.8	12